



200206505-0

ACTION

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

162162

(43) International Publication Date
6 December 2001 (06.12.2001)

PCT

(10) International Publication Number
WO 01/93337 A1(51) International Patent Classification⁷: **H01L 29/737**,
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borough, Hampshire GU14 0LX (GB).

(21) International Application Number: PCT/GB01/02284

(22) International Filing Date: 24 May 2001 (24.05.2001)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
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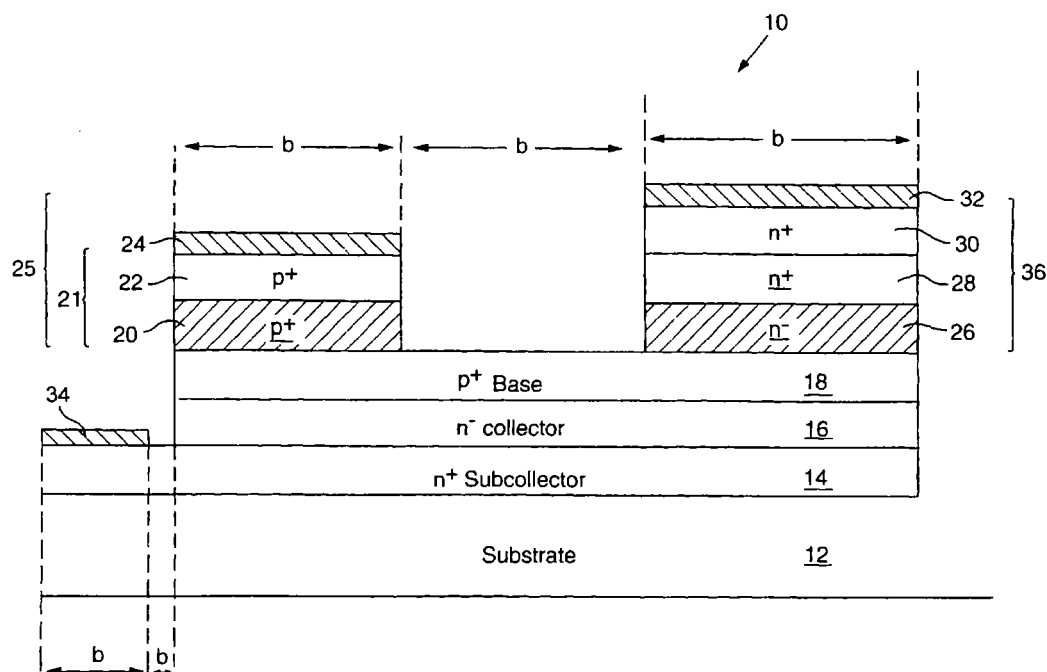
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Malvern, Worcestershire WR14 3PS (GB).(81) Designated States (*national*): AE, AG, AL, AM, AT, AU,
AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU,
CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH,
GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC,
LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW,
MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK,
SL, TJ, TM, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA,
ZW.(84) Designated States (*regional*): ARIPO patent (GH, GM,
KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW), Eurasian
patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European
patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE,
IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF,
CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).

Declaration under Rule 4.17:

— of inventorship (Rule 4.17(iv)) for US only

[Continued on next page]

(54) Title: BIPOLAR TRANSISTOR



WO 01/93337 A1

(57) Abstract: A bipolar transistor having base and collector regions of narrow bandgap semiconductor material and a minority-carrier excluding base contact has a base doping level greater than 10^{17} cm^{-3} . The transistor has a greater dynamic range, greater AC voltage and power gain-bandwidth products and a lower base access resistance than prior art narrow band-gap bipolar transistors.

Published:

- with international search report
- before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments

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